



FORM PTO 1449 (modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary)		ATTY DOCKET NO. 03500.017757.		APPLICATION NO. 10/535,196			
<div style="text-align: center;">  </div>		APPLICANT <div style="text-align: center;">HIDEYA KUMONI</div>					
		FILING DATE <div style="text-align: center;">May 18, 2005</div>		GROUP <div style="text-align: center;">1765</div>			
U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
GAR		2001/0001745 A1	05/24/01	Im et al.	438	747	
		2003/0096489 A1	05/22/03	Im et al.	438	487	
		2003/0119286 A1	06/26/03	Im et al.	438	487	
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		6,555,449 B1	04/29/03	Im et al.	438	487	
		6,322,625 B2	11/27/01	Im	117	43	
		7,029,996 B2	04/18/06	Im et al	438	487	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
GAR	JP	3204986	06/29/01	Japan			US 2001/0001745 A1 US 2003/0096489 A1 US 2003/0119286 A1 US 2005/0255640 A1 US 6,555,449 B1 US 6,322,625 B2 US 7,029,996 B2
OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)							
GAR		A. Hara et al. "High-Performance Polycrystalline Silicon Thin Film Transistors on Non-Alkali Glass Produced Using Continuous Wave Laser Lateral Crystallization", Jpn. J. Appl. Phys., Vol. 41 Part 2, pp. L311-L313 (2002).					
		A. Hara et al. "Large Grain Poly-Si TFTs by Scanning CW Laser Crystallization", AM-LCD '02 Digest of Tech. Paper, pp. 227-230 (2002).					
		M. Tai et al. "Performance of Low Temperature Poly-Si TFTs Fabricated by Selectively Enlarging Laser Crystallization (SELAX)", AM-LCD '02 Digest of Tech. Paper, pp. 231-234 (2002).					
		R. Sposili et al. "Sequential Lateral Solidification of Thin Silicon Films on SiO₂", Appl. Phys. Lett., Vol. 69 No. 19, pp. 2864-2866 (1996).					
		Jin Song H. Et al. "Single-crystal Si Islands on SiO₂ Obtained via Excimer-laser Irradiation of A Patterned Si Film", Appl. Phys. Lett., Vol. 68 No. 22, pp. 3165-3167 (1996).					
EXAMINER				DATE CONSIDERED			
				4/19/07			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO 1449 (modified)

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

LIST OF REFERENCES CITED BY APPLICANT(S)
(Use several sheets if necessary)

ATTY DOCKET NO.

03500.017757.

APPLICATION NO.

PLICATION NO. 107535196

NOT YET ASSIGNED

APPLICANT

HIDEYA KUMONI

FILING DATE

HEREWITH

GROUP

NOT YET ASSIGNED

U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
GAR	EP	1 262 578 A1	12/04/02	EPO			Yes
↓	WO	01/18854 A1	03/15/01	WIPO			Yes
↓	WO	02/086954 A1	10/31/02	WIPO			Yes

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)

GAR		Fortunato G., et al. "Excimer Laser Crystallization Techniques for Polysilicon TFTs", Applied Surface Science, vol. 154-155, pp. 95-104, February 2000.

EXAMINER

DATE CONSIDERED

4/19/07

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